



Advanced Power MOSFET

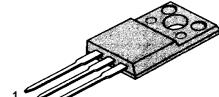
SFS9620

## FEATURES

- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Lower Leakage Current : 10 µA (Max.) @  $V_{DS} = -200V$
- Low  $R_{DS(ON)}$  : 1.111 Ω (Typ.)

 $BV_{DSS} = -200 V$  $R_{DS(on)} = 1.5 \Omega$  $I_D = -3.0 A$ 

TO-220F



1.Gate 2. Drain 3. Source

## Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
$V_{DSS}$	Drain-to-Source Voltage	-200	V
$I_D$	Continuous Drain Current ( $T_C=25^\circ C$ )	-3.0	A
	Continuous Drain Current ( $T_C=100^\circ C$ )	-1.9	
$I_{DM}$	Drain Current-Pulsed	12	A
$V_{GS}$	Gate-to-Source Voltage	$\pm 30$	V
$E_{AS}$	Single Pulsed Avalanche Energy	240	mJ
$I_{AR}$	Avalanche Current	3.0	A
$E_{AR}$	Repetitive Avalanche Energy	2.8	mJ
$dv/dt$	Peak Diode Recovery $dv/dt$	-5.0	V/ns
$P_D$	Total Power Dissipation ( $T_C=25^\circ C$ )	28	W
	Linear Derating Factor	0.22	$W/\text{ }^\circ C$
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ C$
	Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5-seconds	300	

## Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	4.46	$^\circ C/W$
$R_{\theta JA}$	Junction-to-Ambient	--	62.5	

# SFS9620

POWER MOSFET

## Electrical Characteristics ( $T_C=25^\circ\text{C}$ unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	-200	--	--	V	$\text{V}_{\text{GS}}=0\text{V}, \text{I}_D=-250\mu\text{A}$
$\Delta \text{BV}/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	-0.18	--	$\text{V}^\circ\text{C}$	$\text{I}_D=-250\mu\text{A}$ See Fig 7
$\text{V}_{\text{GS(th)}}$	Gate Threshold Voltage	-2.0	--	-4.0	V	$\text{V}_{\text{DS}}=-5\text{V}, \text{I}_D=-250\mu\text{A}$
$\text{I}_{\text{GSS}}$	Gate-Source Leakage , Forward	--	--	-100	nA	$\text{V}_{\text{GS}}=-30\text{V}$
	Gate-Source Leakage , Reverse	--	--	100		$\text{V}_{\text{GS}}=30\text{V}$
$\text{I}_{\text{DSS}}$	Drain-to-Source Leakage Current	--	--	-10	$\mu\text{A}$	$\text{V}_{\text{DS}}=-200\text{V}$
		--	--	-100		$\text{V}_{\text{DS}}=-160\text{V}, \text{T}_C=125^\circ\text{C}$
$\text{R}_{\text{DS(on)}}$	Static Drain-Source On-State Resistance	--	--	1.5	$\Omega$	$\text{V}_{\text{GS}}=-10\text{V}, \text{I}_D=-1.5\text{A}$ ④
$\text{g}_{\text{fs}}$	Forward Transconductance	--	2.1	--	$\Omega$	$\text{V}_{\text{DS}}=-40\text{V}, \text{I}_D=-1.5\text{A}$ ④
$\text{C}_{\text{iss}}$	Input Capacitance	--	415	540	pF	$\text{V}_{\text{GS}}=0\text{V}, \text{V}_{\text{DS}}=-25\text{V}, f=1\text{MHz}$ See Fig 5
$\text{C}_{\text{oss}}$	Output Capacitance	--	70	105		
$\text{C}_{\text{rss}}$	Reverse Transfer Capacitance	--	26	40		
$t_{\text{d(on)}}$	Turn-On Delay Time	--	12	35	ns	$\text{V}_{\text{DD}}=-100\text{V}, \text{I}_D=-3.5\text{A}, \text{R}_G=18\Omega$ See Fig 13 ④ ⑤
$t_r$	Rise Time	--	22	55		
$t_{\text{d(off)}}$	Turn-Off Delay Time	--	33	75		
$t_f$	Fall Time	--	15	40		
$\text{Q}_g$	Total Gate Charge	--	15	19	nC	$\text{V}_{\text{DS}}=-160\text{V}, \text{V}_{\text{GS}}=-10\text{V}, \text{I}_D=-3.5\text{A}$ See Fig 6 & Fig 12 ④ ⑤
$\text{Q}_{\text{gs}}$	Gate-Source Charge	--	3.3	--		
$\text{Q}_{\text{gd}}$	Gate-Drain( " Miller " ) Charge	--	7.5	--		

## Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
$\text{I}_S$	Continuous Source Current	--	--	-3.0	A	Integral reverse pn-diode in the MOSFET
$\text{I}_{\text{SM}}$	Pulsed-Source Current ①	--	--	-12		
$\text{V}_{\text{SD}}$	Diode Forward Voltage ④	--	--	-5.0	V	$\text{T}_J=25^\circ\text{C}, \text{I}_S=-3.0\text{A}, \text{V}_{\text{GS}}=0\text{V}$
$\text{t}_{\text{rr}}$	Reverse Recovery Time	--	125	--	ns	$\text{T}_J=25^\circ\text{C}, \text{I}_F=-3.5\text{A}$ $d\text{I}/dt=100\text{A}/\mu\text{s}$ ④
$\text{Q}_{\text{rr}}$	Reverse Recovery Charge	--	0.59	--		

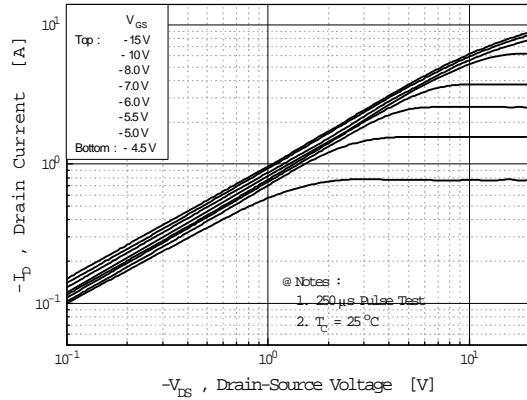
### Notes :

- ① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature
- ②  $L=40\text{mH}, \text{I}_{\text{AS}}=-3.0\text{A}, \text{V}_{\text{DD}}=-50\text{V}, \text{R}_G=27\Omega^*$ , Starting  $\text{T}_J=25^\circ\text{C}$
- ③  $\text{I}_{\text{SD}} \leq 3.5\text{A}, d\text{I}/dt \leq 300\text{A}/\mu\text{s}, \text{V}_{\text{DD}} \leq \text{BV}_{\text{DSS}}$ , Starting  $\text{T}_J=25^\circ\text{C}$
- ④ Pulse Test : Pulse Width = 250  $\mu\text{s}$ , Duty Cycle  $\leq 2\%$
- ⑤ Essentially Independent of Operating Temperature

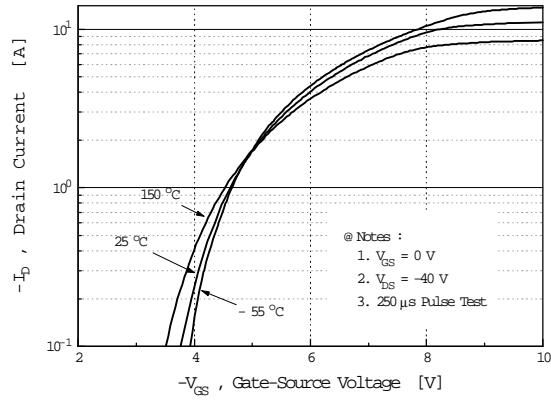
## POWER MOSFET

# SFS9620

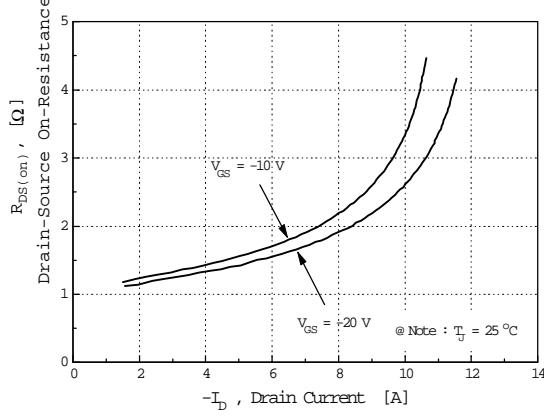
**Fig 1. Output Characteristics**



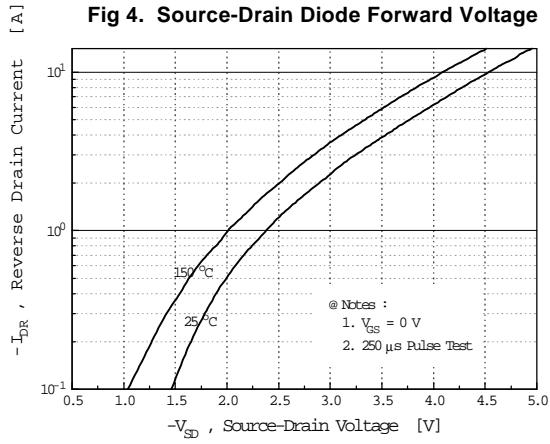
**Fig 2. Transfer Characteristics**



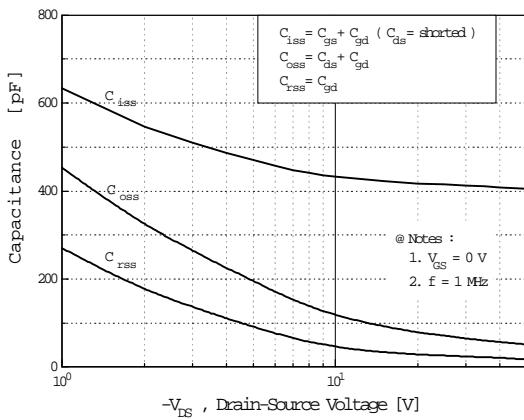
**Fig 3. On-Resistance vs. Drain Current**



**Fig 4. Source-Drain Diode Forward Voltage**



**Fig 5. Capacitance vs. Drain-Source Voltage**



**Fig 6. Gate Charge vs. Gate-Source Voltage**

